

課題番号 : F-16-UT-0026  
 利用形態 : 機器利用  
 利用課題名(日本語) :  
 Program Title (English) : Study on the Cassie-to-Wenzel Transition over MEMS-Based Pillared Surface  
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### 1. 概要(Summary)

The Cassie-to-Wenzel transition needs to be accurately predicted in order to have better design of droplet-based MEMS devices. In the present study, the critical voltage is predicted through 3D simulation for the liquid-air interface of the Cassie state under the electric field. The shape of liquid-air interface is calculated with the Laplace pressure from electric potential and electric field.

### 2. 実験(Experimental)

#### 【利用した主な装置】

高速大面積電子線描画装置, マスク・ウエーハ自動現像装置群, 高速シリコン深掘りエッチング装置, 汎用 ICP エッチング装置

#### 【実験方法】

The fabrication of the present super-lyophobic surface (Fig. 1) includes the equipments of EB-lithography to pattern the mask for pillared surface, CE-300I for CHF<sub>3</sub> plasma etching of SiO<sub>2</sub>, and the MUC-21 for deep etching of pillar structures. The fabrication process is followed by oxidation of Si and coating of hydrophobic layer.

### 3. 結果と考察(Results and Discussion)

A series of experiments are also carried out with MEMS-based Si/SiO<sub>2</sub> and CYTOP pillars, which correspond to the conductive and the dielectric pillars, respectively. The real-time motion of the liquid-air interface is monitored with a high-precision laser displacement meter. The experimental data for the critical voltage are in accordance with the simulation results, verifying the present simulation.

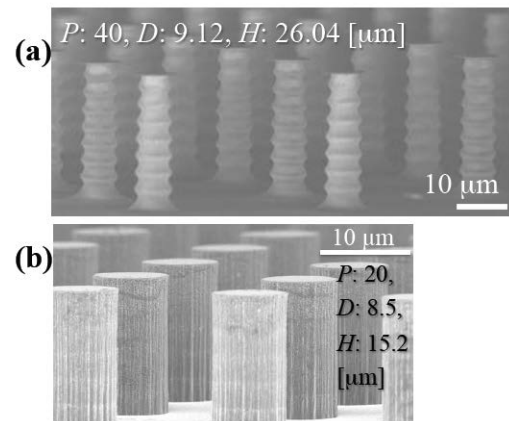


Fig. 1: SEM images: (a) Si/SiO<sub>2</sub> pillar, and (b) CYTOP pillar.

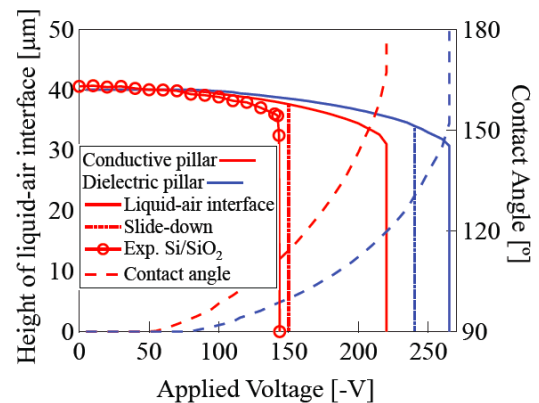


Fig. 2: The liquid-air interface and the contact angle on two types of pillar vs. applied voltage.

### 4. その他・特記事項(Others)

なし

### 5. 論文・学会発表(Publication/Presentation)

(1) Chen, Y.-C., Morimoto, K., and Suzuki, Y., Int. Symp. Micro-Nano Sci. Tech. 2016, Tokyo, SaA1-A-6 (2016).

### 6. 関連特許(Patent)

なし